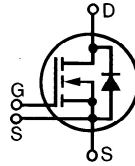


# Polar™ HiPerFET™ Power MOSFET

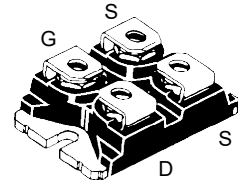
## IXFN140N20P

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



$$\begin{aligned} V_{DSS} &= 200V \\ I_{D25} &= 115A \\ R_{DS(on)} &\leq 18m\Omega \\ t_{rr} &\leq 200ns \end{aligned}$$

miniBLOC  
E153432



G = Gate                      D = Drain  
S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source (Gate Return) Terminal.

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$	200	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$ , $R_{GS} = 1M\Omega$	200	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	115	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$	280	A
$I_A$	$T_C = 25^\circ\text{C}$	60	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	4	J
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 175^\circ\text{C}$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	680	W
$T_J$		-55 ... +175	$^\circ\text{C}$
$T_{JM}$		175	$^\circ\text{C}$
$T_{stg}$		-55 ... +175	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS	$t = 1\text{min}$	2500 V~
	$I_{ISOL} \leq 1\text{mA}$	$t = 1\text{s}$	3000 V~
$M_d$	Mounting Torque	1.5/13	Nm/lb.in
	Terminal Connection Torque	1.3/11.5	Nm/lb.in
<b>Weight</b>		30	g

### Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Low Package Inductance
- Avalanche Rated
- Low  $R_{DS(ON)}$  and  $Q_G$
- Fast Intrinsic Diode

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu\text{A}$	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4\text{mA}$	2.5		V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$			25 $\mu\text{A}$ 250 $\mu\text{A}$
	$T_J = 150^\circ\text{C}$			
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 70A$ , Note 1 $V_{GS} = 15V$ , $I_D = 140A$ , Note 1		14	18 m $\Omega$ m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 70\text{A}$ , Note 1	50	84	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		7500	pF
$C_{oss}$			1630	pF
$C_{rss}$			280	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 70\text{A}$ $R_G = 3.3\Omega$ (External)		30	ns
$t_r$			35	ns
$t_{d(off)}$			150	ns
$t_f$			90	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 70\text{A}$		240	nC
$Q_{gs}$			50	nC
$Q_{gd}$			110	nC
$R_{thJC}$			0.22	$^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

**Source-Drain Diode**

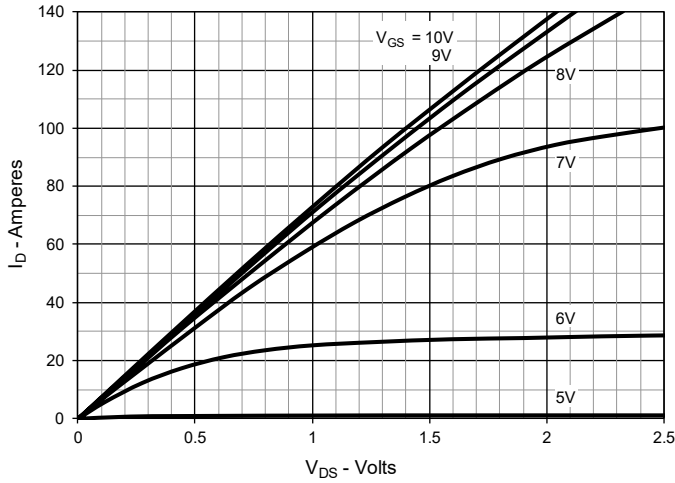
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			140 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			280 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25\text{A}$ , $-di/dt = 150\text{A}/\mu\text{s}$ $V_R = 100\text{V}$			200 ns
$Q_{RM}$			0.6	$\mu\text{C}$
$I_{RM}$			6.0	A

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

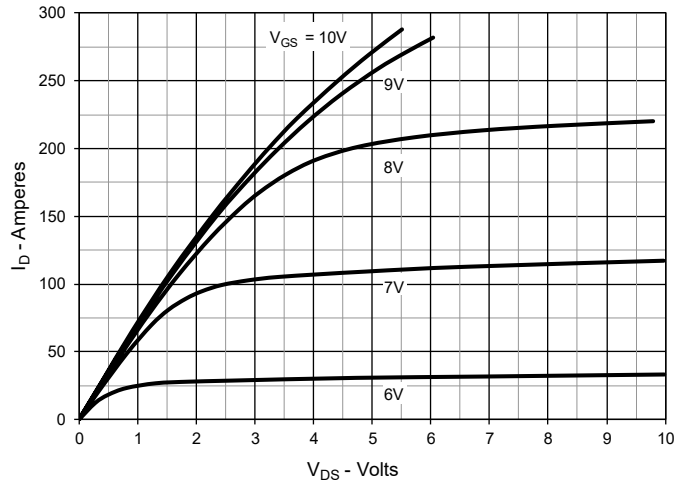
Littelfuse reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

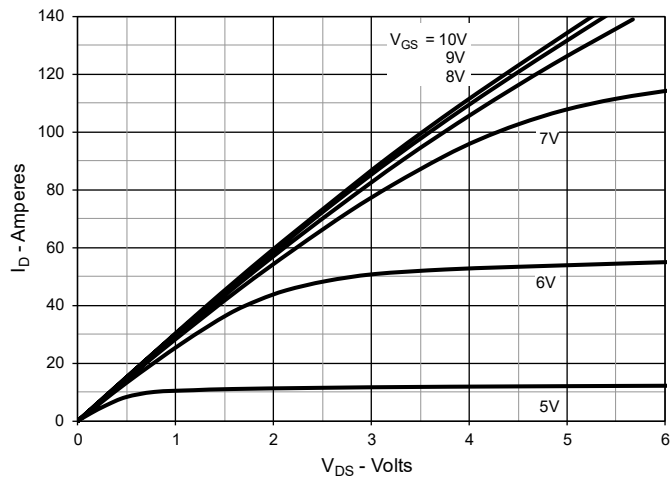
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



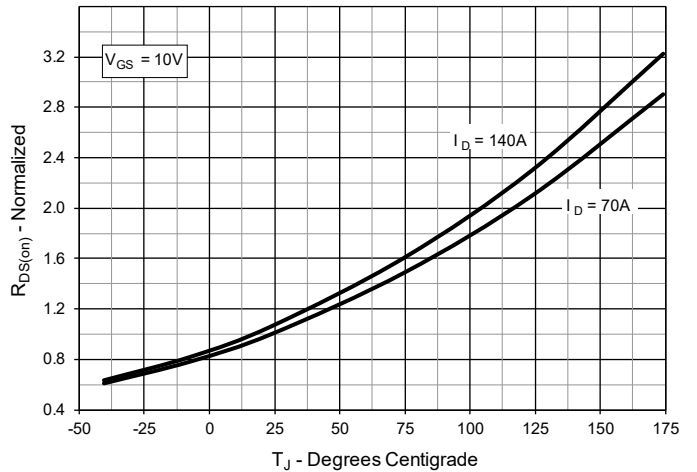
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



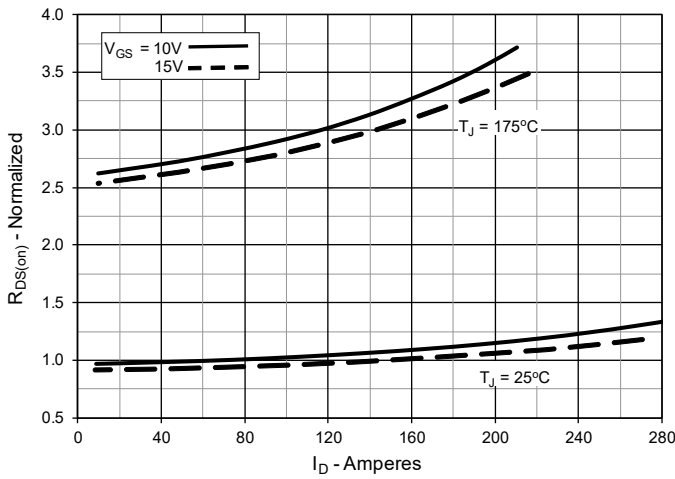
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



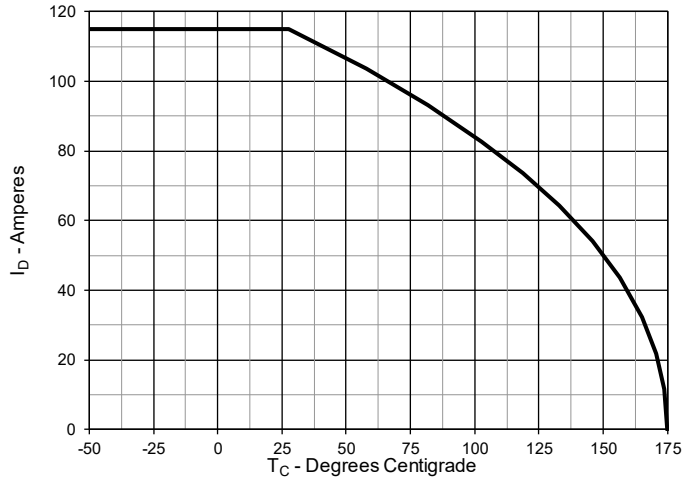
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 70\text{A}$  Value vs. Junction Temperature**



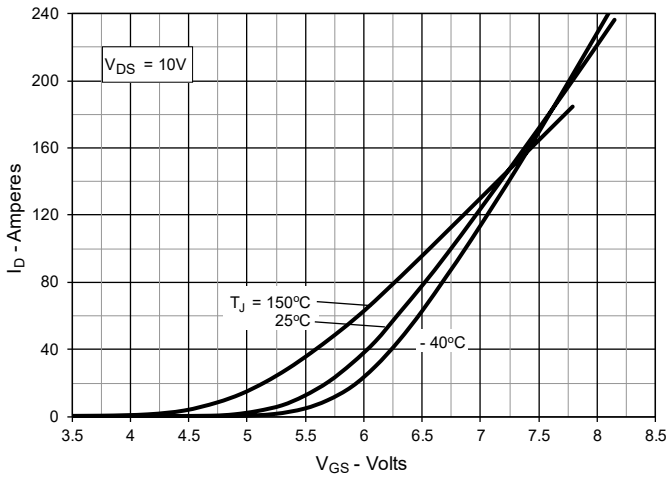
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 70\text{A}$  Value vs. Drain Current**



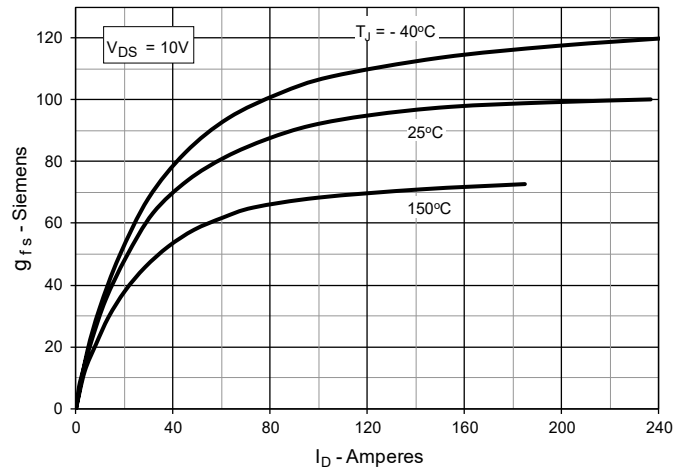
**Fig. 6. Maximum Drain Current vs. Case Temperature**



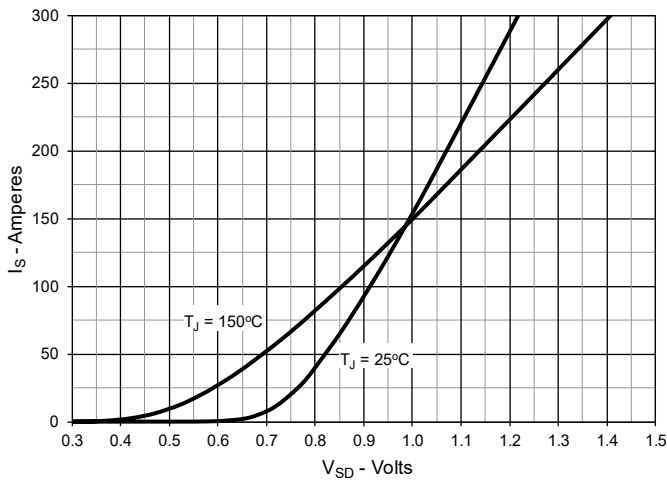
**Fig. 7. Input Admittance**



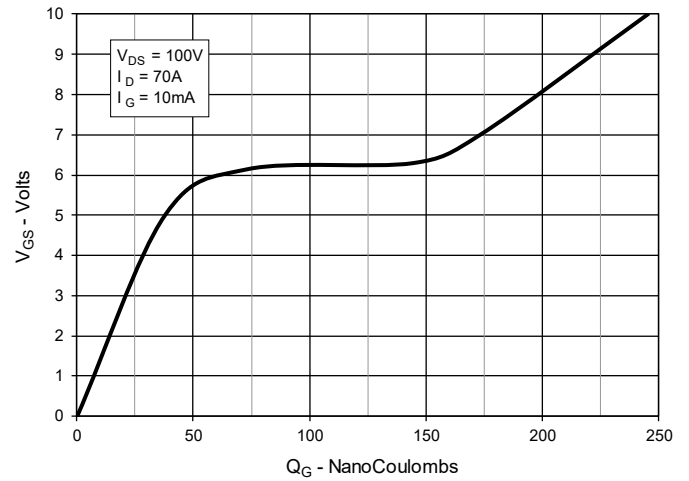
**Fig. 8. Transconductance**



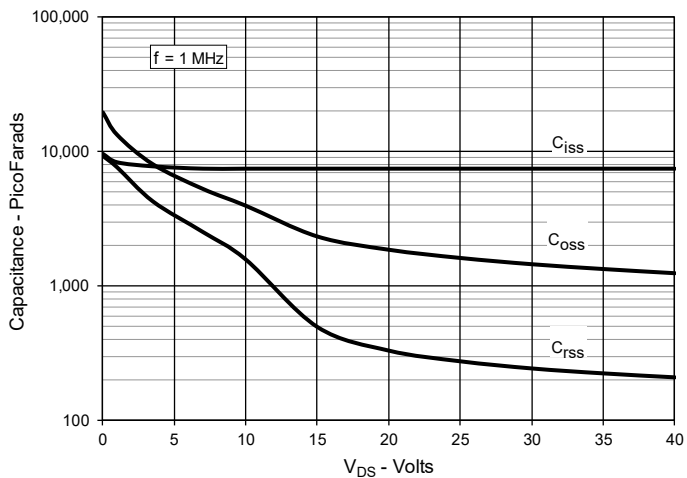
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

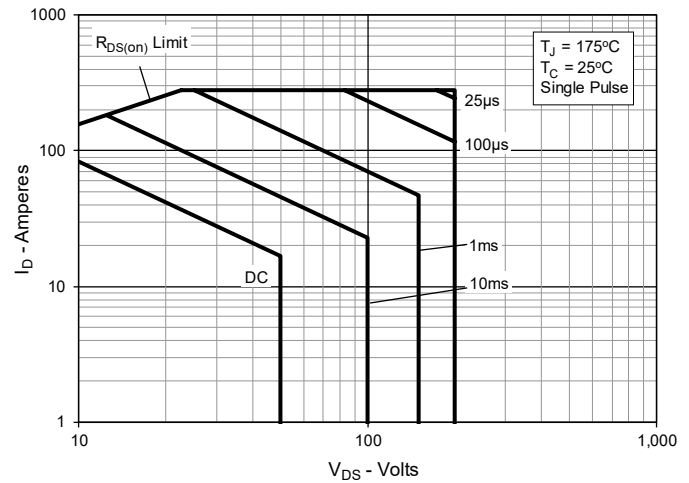
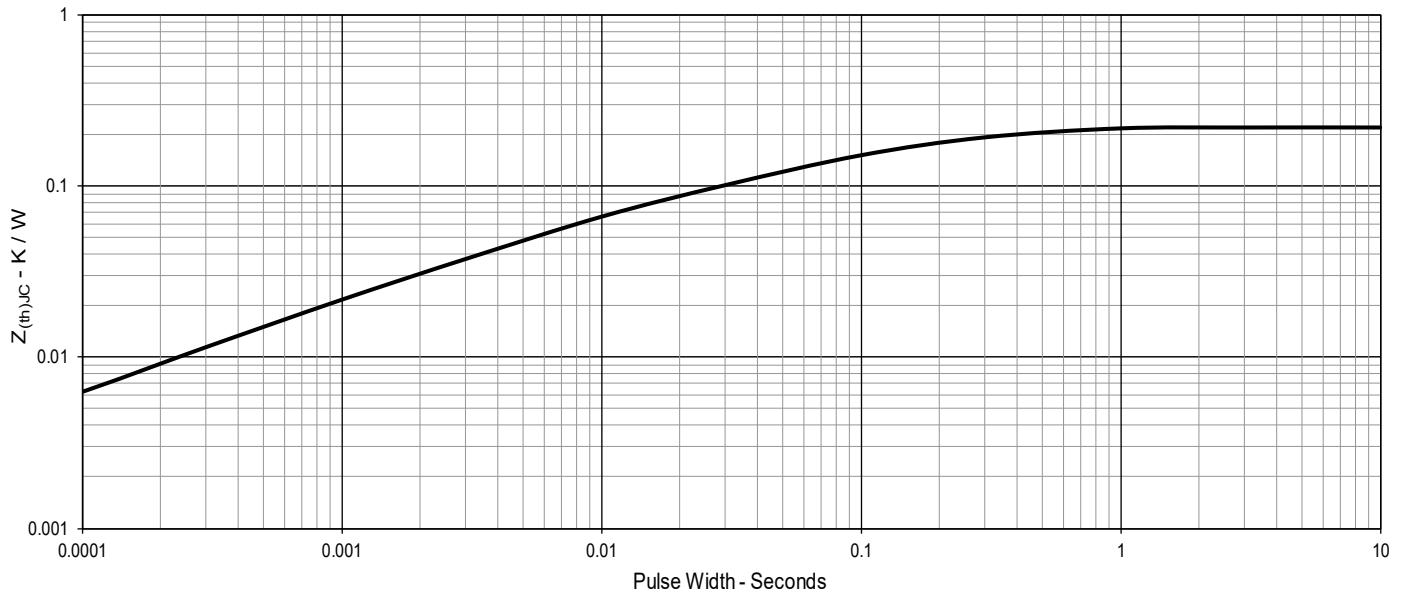
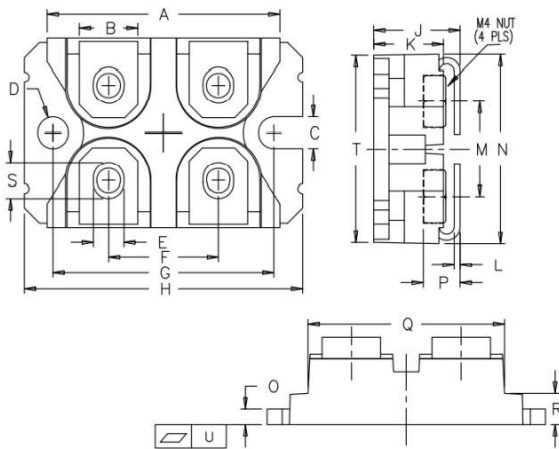


Fig. 13. Maximum Transient Thermal Impedance



**SOT-227 miniBLOC**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1